

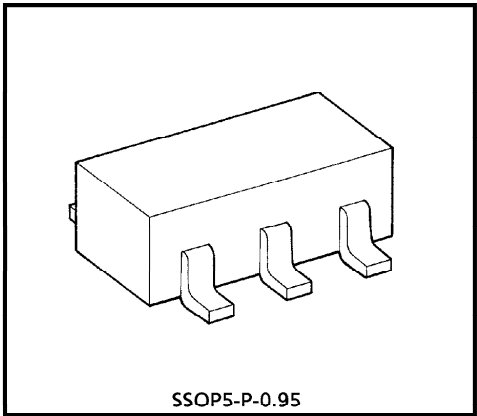
TC4S66F

BILATERAL SWITCH

TC4S66F contains one circuit of bidirectional switches. When control input, CONT is set to "H" level, the impedance between input and output of the switch becomes low and when it is set to "L" level, the switch becomes high. This can be applied for switching of analog signals and digital signals.

FEATURES

- ON-resistance (R_{ON})
 300Ω (Typ.) $V_{DD} - V_{SS} = 5V$
 110Ω (Typ.) $V_{DD} - V_{SS} = 10V$
 70Ω (Typ.) $V_{DD} - V_{SS} = 15V$
- OFF-resistance (R_{OFF})
 R_{OFF} (Typ.) $> 10^9\Omega$



Weight : 0.016g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	$V_{SS} - 0.5 \sim V_{SS} + 20$	V
Control Input Voltage	$V_{C\ IN}$	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
Switch I/O Voltage	$V_{I/O}$	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
Power Dissipation	P_D	200	mW
Potential difference across I/O during ON	$V_I - V_O$	± 0.5	V
Control Input Current	$I_{C\ IN}$	± 10	mA
Operating Temperature Range	T_{opr}	$-40 \sim 85$	$^{\circ}C$
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}C$
Lead Temperature (10s)	T_L	260	$^{\circ}C$

TRUTH TABLE

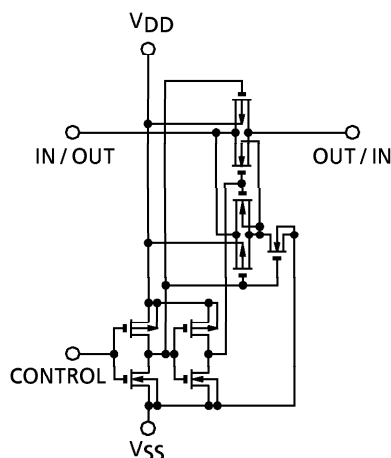
CONTROL	IMPEDANCE BETWEEN IN / OUT-OUT / IN *
H	$0.5 \sim 5 \times 10^2\Omega$
L	$> 10^9\Omega$

* See static electrical characteristics.

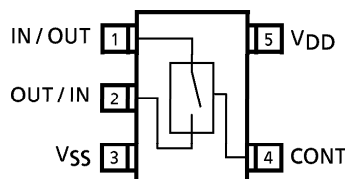
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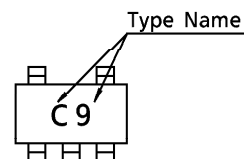
CIRCUIT DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



MARKING

RECOMMENDED OPERATING CONDITIONS ($V_{SS} = 0V$)

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	—	3	—	18	V
Input/Output Voltage	V_{IN}/V_{OUT}	—	0	—	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS (In case not specifically appointed, $V_{SS} = 0V$)

CHARACTERISTIC		SYM- BOL	TEST CONDITION	V _{DD} (V)	- 40°C		25°C			85°C		UNIT
					MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	
Control Input High Voltage		V _{IH}	I _{IS} = 10μA	5	3.5	—	3.5	2.75	—	3.5	—	V
				10	7.0	—	7.0	5.50	—	7.0	—	
				15	11.0	—	11.0	8.25	—	11.0	—	
Control Input Low Voltage		V _{IL}	I _{IS} = 10μA	5	—	1.5	—	2.25	1.5	—	1.5	V
				10	—	3.0	—	4.5	3.0	—	3.0	
				15	—	4.0	—	6.75	4.0	—	4.0	
On-State Resistance		R _{ON}	0 ≤ V _{IS} ≤ V _{DD} R _L = 10kΩ	5	—	800	—	290	950	—	1200	Ω
				10	—	210	—	120	250	—	300	
				15	—	140	—	85	160	—	200	
Input / Output Leakage Current		I _{OFF}	V _{IN} = 18V, V _{OUT} = 0V V _{IN} = 0V, V _{OUT} = 18V	18	—	± 100	—	± 0.1	± 100	—	± 1000	nA
				18	—	± 100	—	± 0.1	± 100	—	± 1000	
Quiescent Device Current		I _{DD}	V _{IN} = V _{DD} , V _{SS}	5	—	0.25	—	0.001	0.25	—	7.5	μA
				10	—	0.5	—	0.001	0.5	—	15	
				15	—	1.0	—	0.002	1.0	—	30	
Input Current	H Level	I _{IH}	V _{IH} = 18V	18	—	0.1	—	10 ⁻⁵	0.1	—	1.0	μA
	L Level	I _{OL}	V _{IL} = 0V	18	—	-0.1	—	-10 ⁻⁵	-0.1	—	-1.0	

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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{SS} (V) V _{DD} (V)		MIN.	TYP.	MAX.	UNIT
			V _{SS} (V)	V _{DD} (V)				
Propagation Delay Time (IN-OUT)	t _{pLH} t _{pHL}	C _L = 50pF	0	5	—	15	40	ns
			0	10	—	8	20	
			0	15	—	5	15	
Propagation Delay Time (CONTROL-OUT)	t _{pZL} t _{pZH}	R _L = 1kΩ C _L = 50pF	0	5	—	55	120	
			0	10	—	25	40	
			0	15	—	20	30	
Propagation Delay Time (CONTROL-OUT)	t _{pLZ} t _{pHZ}	R _L = 1kΩ C _L = 50pF	0	5	—	45	80	
			0	10	—	30	70	
			0	15	—	25	60	
Max. Control Input Repetition Rate	f _{MAX} (C)	R _L = 1kΩ C _L = 50pF	0	5	—	10	—	MHz
			0	10	—	12	—	
			0	15	—	12	—	
– 3dB Cut Off Frequency	f _{MAX} (I-O)	R _L = 1kΩ C _L = 50pF (*1)	– 5	5	—	30	—	
Total Harmonic Distortion	—	R _L = 10kΩ f = 1kHz (*2)	– 5	5	—	0.03	—	%
– 50dB Feedthrough Frequency	—	R _L = 1kΩ (*3)	– 5	5	—	600	—	kHz
Crosstalk (CONTROL-OUT)	—	R _{IN} = 1kΩ R _{OUT} = 10kΩ C _L = 15pF	0	5	—	200	—	mV
			0	10	—	400	—	
			0	15	—	600	—	
Input Capacitance	C _{IN}	Control Input	—	—	—	5	7.5	pF
		Switch I/O	—	—	—	10	—	
Feedthrough Capacitance	C _{IN-OUT}	—	—	—	—	0.5	—	

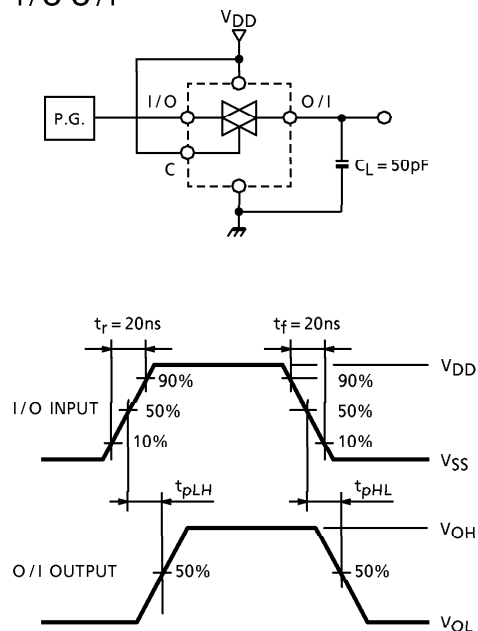
*1 The frequency at $20\log_{10} \frac{V_{OS}}{V_{IS}} = -3\text{dB}$ shall be f_{MAX} (I/O) using sine wave of ±2.5V_{p-p} for V_{IS}.

*2 V_{IS} shall be sine wave of ±2.5V.

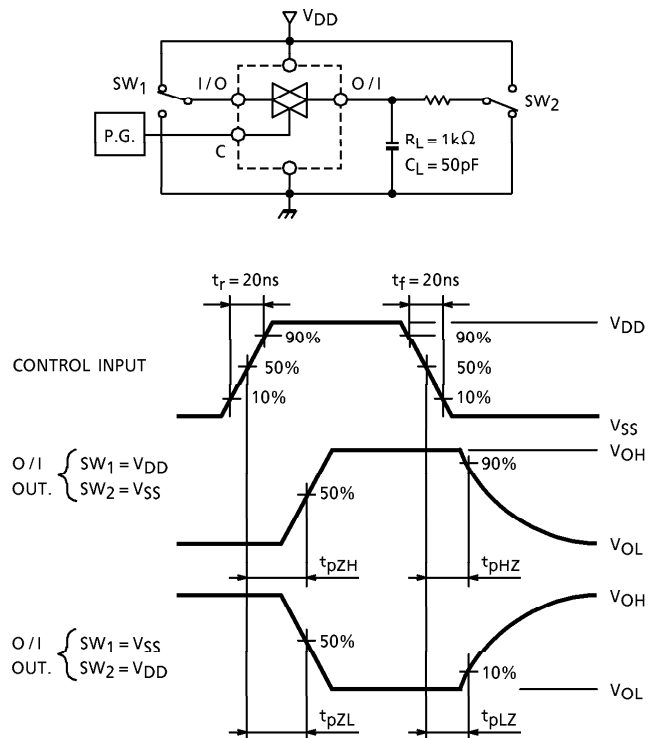
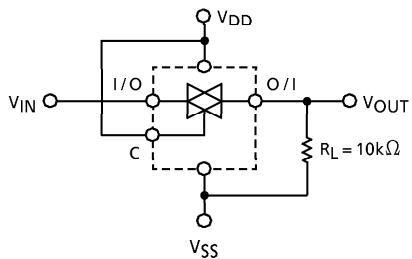
*3 The frequency at $20\log_{10} \frac{V_{OS}}{V_{IS}} = 50\text{dB}$ shall be the feed through using of ±2.5V_{p-p}.

1. t_{pLH} , t_{pHL}

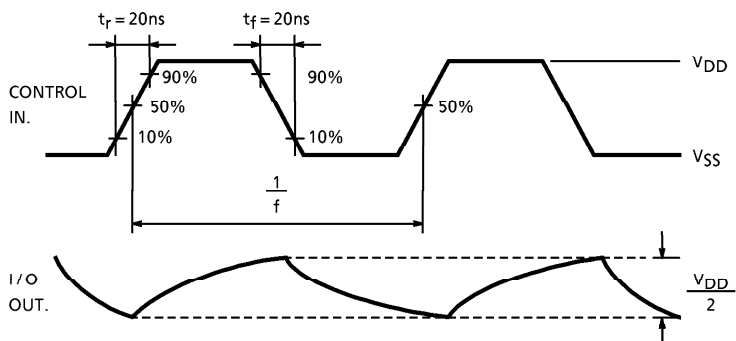
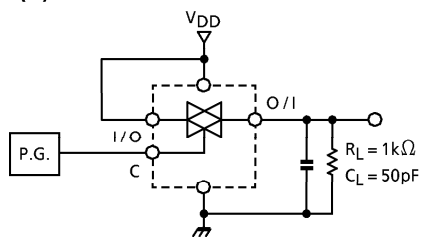
I/O-O/I

2. t_{pZL} , t_{pZH} , t_{pLZ} , t_{pHZ}

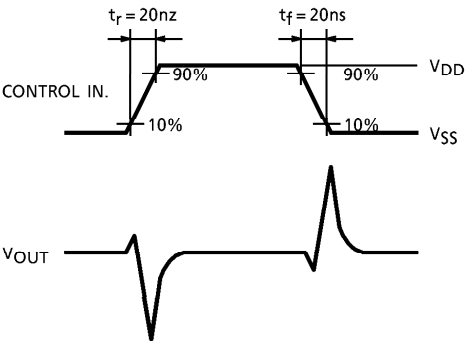
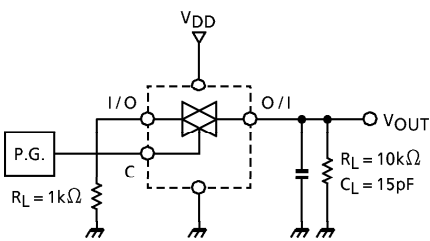
CONTROL-O/I

3. R_{ON} 

$$R_{ON} = 10 \times \frac{(V_{IN} - V_{OUT})}{V_{OUT}} (\text{k}\Omega)$$

4. $f_{MAX}(C)$ 

5. CROSSTALK (CONTROL INPUT)



6. TOTAL HARMONIC DISTORTION, f_{MAX} (I/O-O/I), FEEDTHROUGH (SWITCH OFF)

